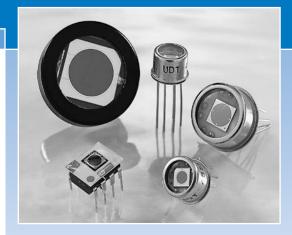
Photodiode-Amplifier Hybrids

The Photop[™] Series, combines a photodiode with an operational amplifier in the same package. Photops[™] general-purpose detectors have a spectral range from either 350 nm to 1100 nm or 200 nm to 1100nm. They have an integrated package ensuring low noise output under a variety of operating conditions. These op-amps are specifically selected by OSI Optoelectronics engineers for compatibility to our photodiodes.

Among many of these specific parameters are low noise, low drift and capability of supporting a variety of gains and bandwidths determined by the external feedback components. Operation from DC level to several MHz is possible in an either unbiased configuration for low speed, low drift applications or biased for faster response time. LN-Series Photops[™] are to be used with OV-bias.

Any modification of the above devices is possible. The modifications can be simply adding a bandpass optical filter, integration of additional chip (hybrid) components inside the same package, utilizing a different op-amp, photodetector replacement, modified package design and / or mount on PCB or ceramic. For your specific requirements, contact one of our Applications Engineers.

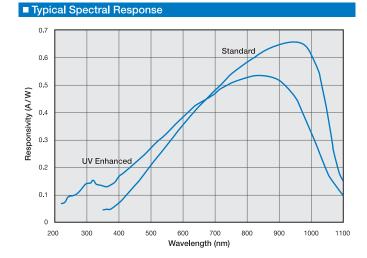


APPLICATIONS

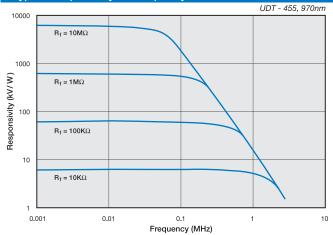
- General Purpose Light
 Detection
- Laser Power Monitoring
- Medical Analysis
- Laser Communications
- Bar Code Readers
- Industrial Control Sensors
- Pollution Monitoring
- Guidance Systems
- Colorimeter

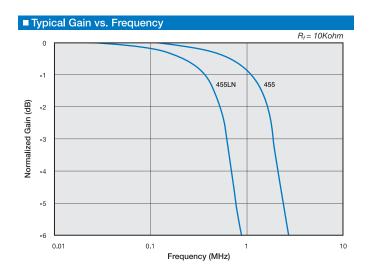
FEATURES

- Detector/Amplifier
 Combined
- Adjustable Gain/Bandwidth
- Low Noise
- Wide Bandwidth
- DIP Package
- Large Active Area









Typical Electro-Optical Specifications at T_A=23°C

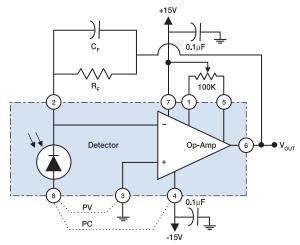
Model Number	Activ	e Area	Responsivity (A/W)				Capacitance (pF)		Dark Current (nA)		Shunt Resistance (MΩ)		EP √Hz)	Reverse Voltage	Terr Rar (°	nge	
	Area (mm²)	Dimension (mm)	254 nm		970 nm		0 V	-10 V			-10 mV	0 V 254 nm	-10 V 970 nm	v	ating	age	Package Style
			min.	typ.	min.	typ.	typ.	typ.	typ.	max.	typ.	typ.	typ.	max.	Operating	Storage	
350-1100 n	350-1100 nm Spectral Range																
UDT-451		2.54 φ			0.60	0.65		15	0.25	3			1.4 e -14 30**			29 / DIP	
UDT-455	5.1						85										
UDT-455LN**	5.1						85							20**			30 / TO-5
OSI-515#														30			
UDT-020D	16	4.57 ø					330	60	0.5	10			1.9 e -14				31 / TO-8
UDT555D	100	11.3 ¢					1500	300	2	25			3.9 e -14		+70	+100	32 / Special
200-1100 nm Spectral Range														30 ~ +			
UDT-455UV	5.1	2.54 ø					300				100	9.2 e -14				ι Υ	30 / TO-5
UDT-455UV/LN**	5.1	2.34 ψ	0.10	0.14			500				100	9.2 e -14					50710-5
UDT-020UV	16	4.57 ¢					1000	1000				1.3 e -13		5**			31 / TO-8
UDT-055UV	50	7.98 ¢	0.10	0.14			2500				20	2.1 e -13					32 / Special
UDT-555UV	100	11.3 ¢					4500				10	2.9 e -13					32 / Special
UDT-555UV/LN**	100						1500										SZ / Special

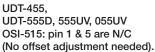
Operational Amplifier Specifications Electro-Optical Specifications at T_A=23 °C

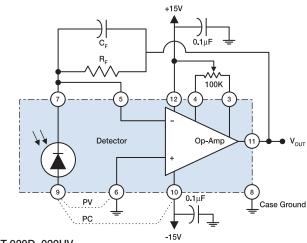
Model Number	Supply Voltage			Quiescent Supply Current (mA) ± 15 V		Input Offset Voltage mV		는 Temp. Coefficient Input Offset Oftset		Input Bias Current pA		Gain Bandwidth Product MHz		Slew Rate V / µs		Open Loop Gain, DC V /mV		Input Noise Voltage [™] NV/ √Hz		Input Noise Current ੈ ਸ fA/ √Hz
	min.	typ.	max.	typ.	max.	typ.	max.	typ.	max.	typ.	max.	min.	typ.	min.	typ.	min.	typ.	typ.	typ.	typ.
UDT-451		±15	±18	1.4	2.5	3.0	6.0	10		30	200		4.0		13	50	150		18	10
UDT-455		±15	±18	2.8	5.0	0.5	3	4	30	±80	±400	3.0	5.4	5	9	50	200	20	15	
UDT-455UV																				10
UDT-020D																				10
UDT-020UV																				
OSI-515#		±15	±18	6.5	7.2	1	3	10		±15	±40	23	26	125	140	3	6.3		12	10
UDT-455LN**	±5	±15	±18	0.9	1.8	0.26	1		20	0.15	0.3	0.5	1	0.5	3	50	2500	78	27	0.22
UDT-455UV/LN**	70	-15	- 10	0.9	1.0	0.20	1		20	0.15	0.5	0.5		0.5	3	50	2,500	70	27	0.22
UDT-055UV																				
UDT-555D		±15	±22	2.7	4.0	0.4	1	3	10	±40	±200	3.5	5.7	7.5	11	75	220	20	15	10
UDT-555UV																				

¶ For mechanical drawings please refer to pages 58 thru 69.
 ** LN - Series Devices are to be used with a 0V Bias.
 * Non-Condensing temperature and Storage Range, Non-Condensing Environment.

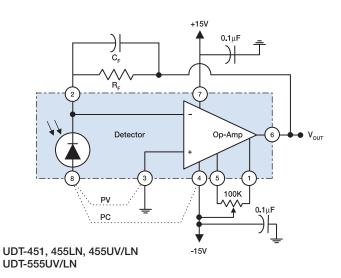
OSI-515 replaces UDT-455HS







UDT-020D, 020UV



The output voltage is proportional to the light intensity of the light and is given by:

$$V_{OUT} = I_P \times R_F$$

= $(P \times R_{\lambda}) \times R_F$ (1)

Frequency Response (Photodiode/Amplifier Combination)

The frequency response of the photodiode / amplifier combination is determined by the characteristics of the photodetector, pre-amplifier as well as the feedback resistor (R_F) and feedback capacitor (C_F). For a known gain, (R_F), the 3dB frequency response of the detector/pre-amp combination is given by:

$$f_{3dB} = \frac{1}{2\pi C_F R_F} \tag{2}$$

However, the desired frequency response is limited by the Gain Bandwidth Product (GBP) of the op-amp. In order to have a stable output, the values of the R_F and C_F must be chosen such that the 3dB frequency response of the detector / pre-amp combination, be less than the maximum frequency of the op-amp, i.e. $f_{adB} \leq f_{max}$.

$$f_{\max} = \sqrt{\frac{GBP}{2\pi R_F (C_F + C_J + C_A)}}$$
(3)

where C_A is the amplifier input capacitance.

In conclusion, an example for frequency response calculations, is given below. For a gain of 10^8 , an operating frequency of 100 Hz, and an opamp with GBP of 5 MHz:

$$C_F = \frac{1}{2\pi f_{3dB}R_F} = 15.9pF$$
(4)

Thus, for $C_{_F}$ = 15.9 pF, $C_{_J}$ = 15 pF and $C_{_A}$ = 7 pF, $f_{_{max}}$ is about 14.5 kHz. Hence, the circuit is stable since $f_{_{3dB}}$ = $f_{_{max}}$.

For more detailed application specific discussions and further reading, refer to the APPLICATION NOTES INDEX in the catalog.

Note: The shaded boxes represent the Photop[™] components and their connections. The components outside the boxes are typical recommended connections and components.

1. Parameter Definitions:

- A = Distance from top of chip to top of glass.
- a = Photodiode Anode.
- B = Distance from top of glass to bottom of case.
- c = Photodiode Cathode
 - (Note: cathode is common to case in metal package products unless otherwise noted).
- W = Window Diameter.
- F.O.V. = Filed of View (see definition below).

2. Dimensions are in inches (1 inch = 25.4 mm).

3. Pin diameters are 0.018 ± 0.002" unless otherwise specified.

4. Tolerances (unless otherwise noted) General: 0.XX ±0.01" 0.XXX ±0.005" Chip Centering: ±0.010"

Dimension 'A': ± 0.015 "

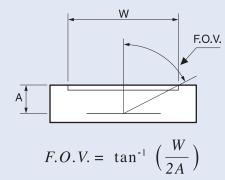
5. Windows

All '**UV**' Enhanced products are provided with QUARTZ glass windows, 0.027 \pm 0.002" thick.

All 'XUV' products are provided with removable windows.

All '**DLS**' PSD products are provided with A/R coated glass windows.

All 'FIL' photoconductive and photovoltaic products are epoxy filled instead of glass windows.





Mechanical Specifications and Die Topography

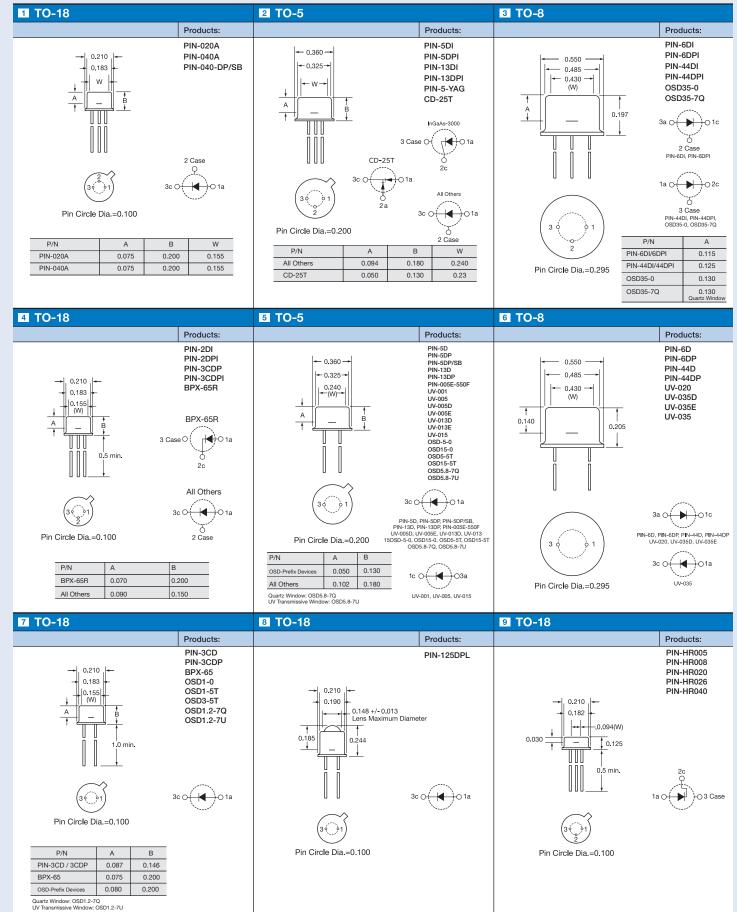
For Further Assistance Please Call One of Our Experienced Sales and Applications Engineers

310-978-0516

- Or -On the Internet at WWW.OSioptoelectronics.com

Mechanical Specifications

All units in inches. Pinouts are bottom view.



Mechanical Specifications

All units in inches. Pinouts are bottom view.

